

BC527 · BC528

PNP SILICON AF MEDIUM POWER TRANSISTORS

THE BC527, BC528 ARE PNP SILICON PLANAR EPITAXIAL TRANSISTORS FOR USE IN AF DRIVER AND OUTPUT STAGES, AS WELL AS FOR UNIVERSAL APPLICATIONS. THE BC527, BC528 ARE COMPLEMENTARY TO THE NPN TYPE BC537, BC538 RESPECTIVELY.

CASE TO-92A

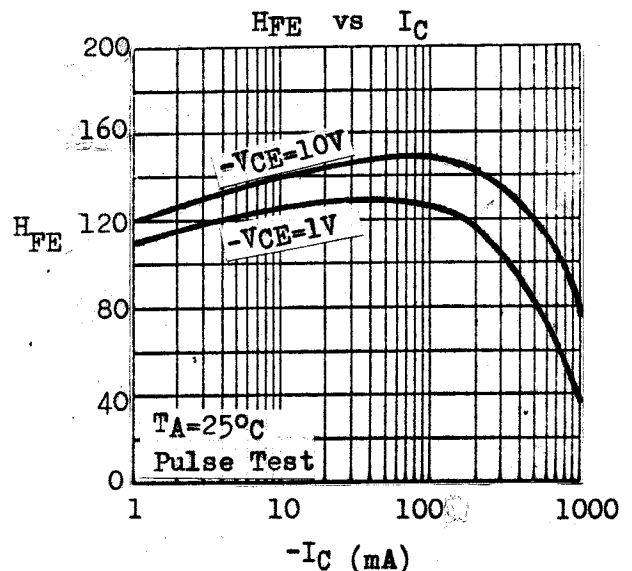
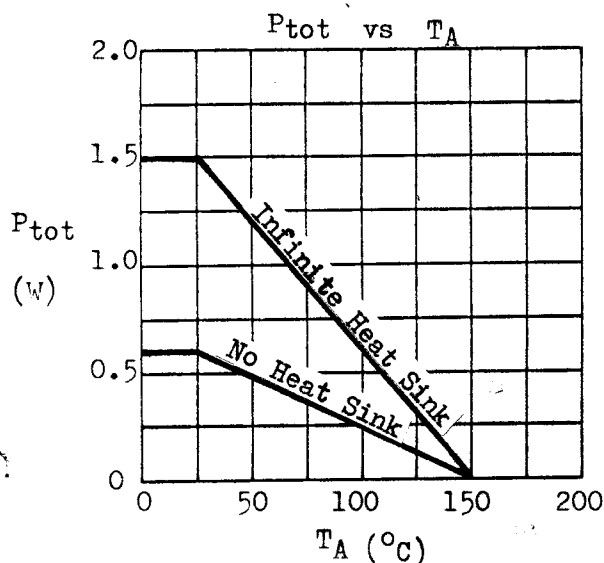


ABSOLUTE MAXIMUM RATINGS

		BC527	BC528
Collector-Base Voltage	$-V_{CBO}$	60V	80V
Collector-Emitter Voltage	$-V_{CEO}$	60V	80V
Emitter-Base Voltage	$-V_{EBO}$	6V	
Collector Current	$-I_C$	1A	
Collector Peak Current ($t \leq 10\text{ms}$)	$-I_{CM}$	1.5A	
Total Power Dissipation (@ $T_C \leq 25^\circ\text{C}$)	P_{tot}	1.5W	
(@ $T_A \leq 25^\circ\text{C}$)		625mW	
Operating Junction & Storage Temperature	T_j, T_{stg}	-55 to 150°C	

THERMAL RESISTANCE

Junction to Case	θ_{jc}	83°C/W max.
Junction to Ambient	θ_{ja}	200°C/W max.



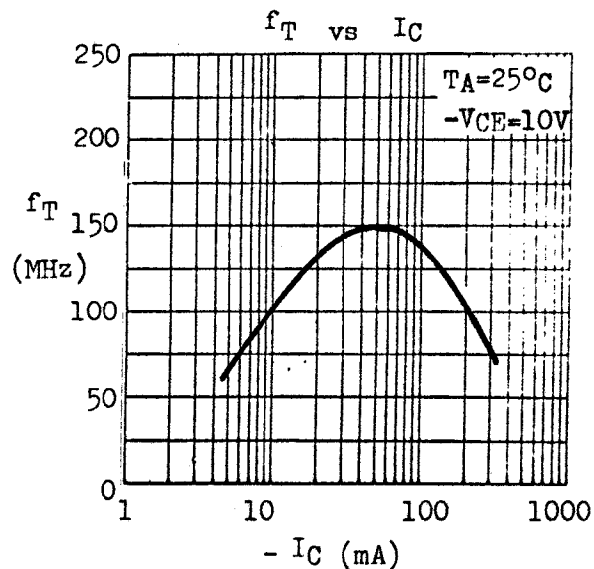
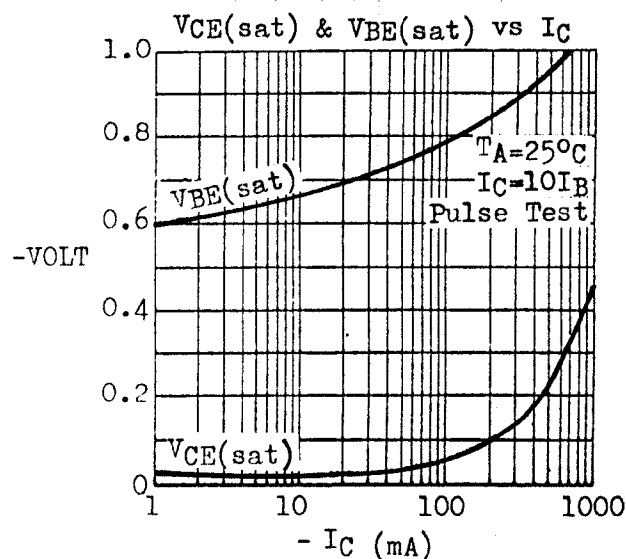
MICRO ELECTRONICS LTD.

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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	BC527		BC528		UNIT	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
Collector-Base Breakdown Voltage	$-BV_{CBO}$	60		80		V	$-I_C=0.1\text{mA}$ $I_E=0$
Collector-Emitter Breakdown Voltage	$-LV_{CEO} *$	60		80		V	$-I_C=10\text{mA}$ $I_B=0$
Emitter-Base Breakdown Voltage	$-BV_{EBO}$	6		6		V	$-I_E=0.01\text{mA}$ $I_C=0$
Collector Cutoff Current	$-I_{CBO}$		100		100	nA	$-V_{CB}=40\text{V}$ $I_E=0$
						nA	$-V_{CB}=60\text{V}$ $I_E=0$
Emitter Cutoff Current	$-I_{EBO}$		100		100	nA	$-V_{EB}=4\text{V}$ $I_C=0$
						nA	$-V_{EB}=4\text{V}$ $I_C=0$
Collector-Emitter Saturation Voltage	$-V_{CE}(\text{sat}) *$		0.7 1.2		0.7 1.5	V	$-I_C=500\text{mA}$ $-I_B=50\text{mA}$
						V	$-I_C=1\text{A}$ $-I_B=0.1\text{A}$
Base-Emitter Saturation Voltage	$-V_{BE}(\text{sat}) *$		1.3		1.3	V	$-I_C=150\text{mA}$ $-I_B=15\text{mA}$
						V	$-I_C=150\text{mA}$ $-I_B=15\text{mA}$
D.C. Current Gain	$H_{FE} *$	40	400	40	400		$-I_C=100\text{mA}$ $-V_{CE}=1\text{V}$
		40	100	40	100		
		63	160	63	160		
		100	250	100	250		
		160	400	160	400		
All Groups	$H_{FE} *$	50		50			$-I_C=10\text{mA}$ $-V_{CE}=10\text{V}$
		50		50			$-I_C=150\text{mA}$ $-V_{CE}=10\text{V}$
		50		50			$-I_C=500\text{mA}$ $-V_{CE}=10\text{V}$
		15		15			$-I_C=1\text{A}$ $-V_{CE}=10\text{V}$
Current Gain-Bandwidth Product	f_T	100		100		MHz	$-I_C=50\text{mA}$ $-V_{CE}=10\text{V}$
Collector-Base Capacitance	C_{ob}		15		15	pF	$-V_{CB}=10\text{V}$ $I_E=0$ $f=1\text{MHz}$

* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%



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